



#### 30V PNP LOW SATURATION TRANSISTOR IN SOT223

#### **Features**

- BV<sub>CEO</sub> > -30V
- I<sub>C</sub> = -5.5A Continuous Collector Current
- I<sub>CM</sub> = -20A Peak Pulse Current
- Low Saturation Voltage V<sub>CE(SAT)</sub> < -60mV max @ -1A</li>
- R<sub>SAT</sub> = 31mΩ @ -5.5A for Low Equivalent On-Resistance
- Exceptional Gain Linearity Down to -10mA
- h<sub>FE</sub> Specified up to -20A for High Gain Hold Up
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

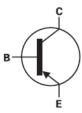
- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound.
   UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 (§3)
- Weight: 0.112 grams (Approximate)

### **Applications**

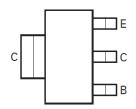
- DC-DC Converters
- MOSFET Gate Drivers
- Charging Circuits
- Power Switches
- Motor Control



Top View



**Device Schematic** 



Pin-Out Top View

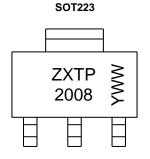
### Ordering Information (Note 4)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
ZXTP2008GTA	ZXTP2008	7	12	1,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## Marking Information



ZXTP 2008 = Product Type Marking Code YWW = Date Code Marking Y or  $\overline{Y}$  = Last Digit of Year (ex: 5= 2015) WW or  $\overline{W}W$  = Week Code (01 - 53)



# Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-50	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-30	V
Emitter-Base Voltage	V <sub>EBO</sub>	-7	V
Continuous Collector Current	Ic	-5.5	A
Peak Pulse Current	I <sub>CM</sub>	-20	A

### Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 5)		3.0 24	W mW/°C
Linear Derating Factor	(Note 6)	P <sub>D</sub>	1.6 12.8	
Thermal Resistance, Junction to Ambient	(Note 5)	R <sub>0JA</sub>	42	
Thermal Resistance, Junction to Ambient	(Note 6)	R <sub>0JA</sub>	78	°C/W
Thermal Resistance, Junction to Lead	(Note 7)	$R_{\theta JL}$	8.8	
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

## ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge – Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge – Machine Model	ESD MM	400	V	С

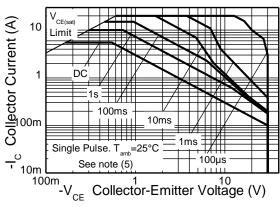
- 5. For a device mounted with the collector lead on 52mm x 52mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady-state.

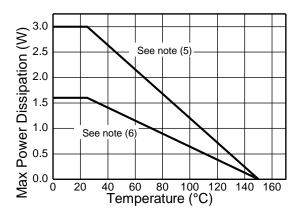
  6. Same as Note 5, except the device is mounted on 25mm x 25mm 1oz copper.
- 7. Thermal resistance from junction to solder-point (at the end of the collector lead).

  8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



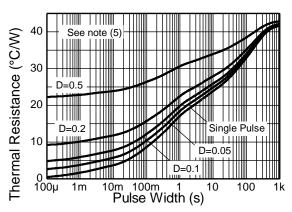
### **Thermal Characteristics and Derating Information**

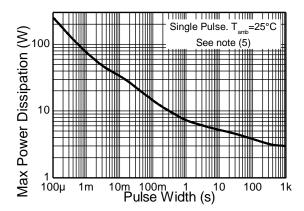




**Safe Operating Area** 

**Derating Curve** 





**Transient Thermal Impedance** 

**Pulse Power Dissipation** 



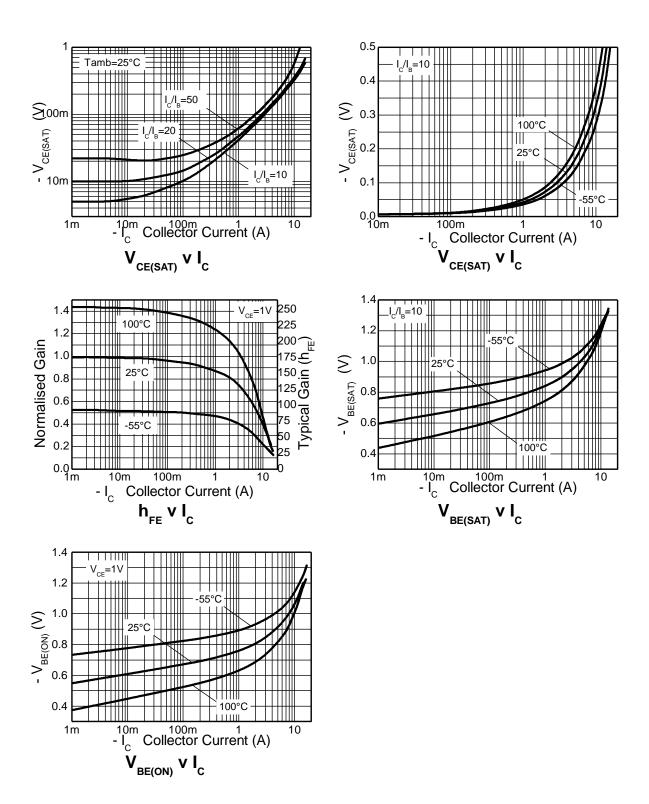
# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	$BV_{CBO}$	-50	-70	_	V	$I_{C} = -100 \mu A$
Collector-Emitter Breakdown Voltage	BV <sub>CER</sub>	-50	-70	_	V	$I_C = -1\mu A, R_B \le 1k\Omega$
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	-30	-40	_	V	I <sub>C</sub> = -10mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-7	-8	_	V	$I_E = -100 \mu A$
Collector Cutoff Current	I <sub>CBO</sub>	_	< -1	-20	nA	V <sub>CB</sub> = -40V
Collector Guton Gurrent	ICBO	_	_	-0.5	μA	$V_{CB} = -40V, T_A = +100^{\circ}C$
Collector Cutoff Current	I <sub>CER</sub>	_	< -1	-20	nA	$V_{CB} = -40V$
	R≤1kΩ	_	_	-0.5	μA	$V_{CB} = -40V, T_A = +100^{\circ}C$
Emitter Cutoff Current	I <sub>EBO</sub>	_	< -1	-10	nA	$V_{EB} = -6V$
			-30	-45		$I_C = -0.5A$ , $I_B = -20mA$
	V <sub>CE</sub> (SAT)	_	-40	-60		$I_C = -1A$ , $I_B = -100mA$
Collector-Emitter Saturation Voltage (Note 9)			-60	-85		$I_C = -1A$ , $I_B = -20mA$
			-70	-90		$I_C = -2A$ , $I_B = -200mA$
			-170	-210		$I_C = -5.5A$ , $I_B = -500mA$
Base-Emitter Saturation Voltage (Note 9)	V <sub>BE(SAT)</sub>	_	-1.03	-1.13	V	$I_C = -5.5A$ , $I_B = -500mA$
Base-Emitter Turn-On Voltage (Note 9)	V <sub>BE(ON)</sub>	_	-0.9	-1	V	$I_C = -5.5A$ , $V_{CE} = -1V$
	h <sub>FE</sub>	100	225			I <sub>C</sub> = -10mA, V <sub>CE</sub> = -1V
DC Current Gain (Note 9)		100	200	300		$I_C = -1A$ , $V_{CE} = -1V$
DC Current Gain (Note 9)		70	145		_	$I_C = -5A$ , $V_{CE} = -1V$
		10	20			$I_C = -20A$ , $V_{CE} = -1V$
Transition Frequency	f⊤	_	110		MHz	$V_{CE} = -10V, I_{C} = -100mA,$
	''					f = 50MHz
Output Capacitance (Note 9)	Сово	_	83	_	pF	$V_{CB} = -10V$ , $f = 1MHz$
Switching Times	ton	_	43	_	ns	$V_{CC} = -10V, I_{C} = -1A,$
Ownering Times	toff	_	230	_	113	$I_{B1} = -I_{B2} = 100 \text{mA}$

Note: 9. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%.



## Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

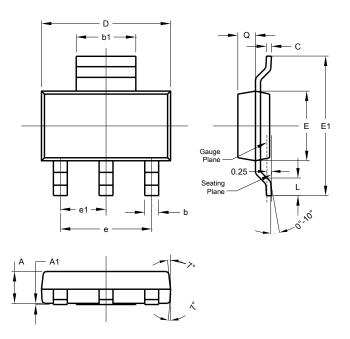




# **Package Outline Dimensions**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

#### **SOT223**

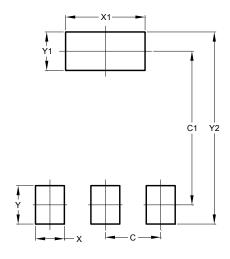


SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

#### **SOT223**



Dimensions	Value (in mm)			
С	2.30			
C1	6.40			
Х	1.20			
X1	3.30			
Υ	1.60			
Y1	1.60			
C2	8.00			



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